

Form PTO-1449				Attorney Docket No. 062002-1752		Serial No. To Be Assigned	
INFORMATION DISCLOSURE CITATION				Applicant Martin, et al.		10/784697	
<i>(Use several sheets if necessary)</i>				Filing Date Even Date Herewith		Group 1763	
U.S. PATENT DOCUMENTS							
Examiner Initials	Item	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>MJP</i>	1A	1,712,407	5/7/1929	Skaupy			
<i>MJP</i>	1B	2,037,075	4/14/1936	Haines	250	27.5	
<i>MJP</i>	1C	3,304,456	2/14/1967	De Lany et al.	313	182	
<i>MJP</i>	1D	3,879,597	4/22/1975	Bersin et al.	219	121	
<i>MJP</i>	1E	4,031,424	6/21/1977	Penfold et al.	313	146	
<i>MJP</i>	1F	4,207,158	6/10/1980	Freeman	204	180	
<i>MJP</i>	1G	4,259,145	3/31/1981	Harper et al.	156	643	
<i>MJP</i>	1H	4,298,443	11/3/1981	Maydan	204	192	
<i>MJP</i>	1I	4,309,267	1/5/1982	Boyd et al.	204	298	
<i>MJP</i>	1J	4,450,787	5/29/1984	Weakliem et al.	118	723	
<i>MJP</i>	1K	4,464,223	05/1999	Gorin	438	729	
<i>MJP</i>	1L	4,496,881	1/29/1985	Cheever	315	357	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	1M						
	1N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>MJP</i>	1O	P. Breisacher et al. "Comparative Stabilities of Gaseous Alane. Gallane and Indane" Journal of the American Chemical Society pp. 4255-4258 87:19 Oct 5, 1965.					
<i>MJP</i>	1P	S. Veprek et al. "The Preparation of Thin Layers of Ge and Si by Chemical Hydrogen Plasma Transport." Solid-State Electronics Pergamon Press 1968 vol. 11 pp. 683-684.					
<i>MJP</i>	1Q	E. Wiberg et al "Hydrides of the Elements of Main Groups I-IV" New York 1971 Chapter 6 pp. 443-460.					
<i>MJP</i>	1R	A.P. Webb "Reactivity of Solid Silicon with Hydrogen Under Conditions of a Low Pressure Plasma." Chemical Physics Letters vol 62 No 1 Mar 15, 1979 pp 173-177.					
<i>MJP</i>	1W	S. Veprek et al. "Parameters Controlling the Deposition of Amorphous and Microcrystalline Silicon in Si/H Discharge Plasmas." Journal De Physique (Paris) 42 C4-251 (1981).					
* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							
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<i>WJP</i>	2A	4,609,428	9/2/1986	Fujimara	156	643	
<i>WJP</i>	2B	4,863,549	09/1989	Grunwald, Henrich	156	345.44	
<i>WJP</i>	2C	4,871,580	10/3/1989	Schram et al.	427	38	
<i>WJP</i>	2D	4,874,459	10/17/1989	Coldren et al.	156	643	
<i>WJP</i>	2E	4,891,118	01/1990	Ooiwa et al.	204	298.34	
<i>WJP</i>	2F	5,003,178	3/26/1991	Livesay	250	492.300	
<i>WJP</i>	2G	5,039,376	8/13/1991	Zukotynski et al.	156	643	
<i>WJP</i>	2H	5,138,169	8/11/1992	Yamazaki et al.	250	398	
<i>WJP</i>	2I	5,145,554	9/8/1992	Seki et al.	156	643	
<i>WJP</i>	2J	5,241,535	8/31/1993	Yoshikawa	370	60	
<i>WJP</i>	2K	5,290,993	03/1994	Kaji et al.	219	121.43	
<i>WJP</i>	2L	5,298,896	3/29/1994	Lei et al.	341	51	
<i>WJP</i>	2M	5,309,232	5/3/1994	Hartung et al.	348	384	

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						Yes No
	2N					
	2O					

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>WJP</i>	2P	S. Veprek et al "Electron-Impact-Induced Anisotropic Etching of Silicon by Hydrogen" Plasma Chemistry and Plasma Processing vol. 2 No 3 1982.
<i>WJP</i>	2Q	S. Veprek "Highlights of Preparative Solid State Chemistry in Low Pressure Plasmas." Pure & Appl. Chem. Vol. 54 No. 6 pp. 1197-1220. 1982.
<i>WJP</i>	2R	J.R. Creighton "Hydrogen Chemisorption and Reaction on GaAs(100)." J. Vac. Sci. Technol. A 8 (6) Nov/Dec 1990 pp. 3984-3987.
<i>WJP</i>	2S	H.P. Gillis et al "Low-Energy Electron Beam Enhanced Etching of Si(100)-(2x1) by Molecular Hydrogen" J. Vac. Sci. Technol B. vol. 10 No. 6. Nov/Dec 1992.
<i>WJP</i>	2T	H. Watanabe et al "Electron-beam-assisted Dry Etching for GaAs using Electron Cyclotron Resonance Plasma Electron Source" Appl Phys. Lett 61 (25) Dec 21, 1992 pp. 3011-3013.

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EXAMINER'S SIGNATURE:

Walter J. Chambers

DATE CONSIDERED:

6/9/2005

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<i>mjr</i>	3A	5,310,452	05/1994	Doki et al.	438	728	
<i>mjr</i>	3B	5,331,249	7/19/1994	Minamikata et al.	313	632	
<i>mjr</i>	3C	5,352,953	10/4/1994	Wakabayashi et al.	313	631	
<i>mjr</i>	3D	5,368,676	11/29/1994	Nagaseki et al.	156	345	
<i>mjr</i>	3E	5,418,423	5/23/1995	Murray	313	589	
<i>mjr</i>	3F	5,453,305	9/26/1995	Lee	427	562	
<i>mjr</i>	3G	5,457,298	10/10/1995	Nelson et al.	219	121.52	
<i>mjr</i>	3H	5,485,210	1/16/1996	Lim et al.	348	409	
<i>mjr</i>	3I	5,497,053	3/5/1996	Tang et al.	315	366	
<i>mjr</i>	3J	5,556,501	9/17/1996	Collins et al.	156	345	
<i>mjr</i>	3K	5,572,088	11/5/1996	Aizawa et al.	313	491	
<i>mjr</i>	3L	5,606,370	2/25/1997	Moon	348	390	
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							Yes No
	3M						
	3N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>mjr</i>	3O	K. Choquette et al "Hydrogen Plasma Processing of GaAs and AlGaAs" J. Vac. Sci. Technol B. vol 11 No. 6 Nov/Dec 1993 pp 2025-2032.					
<i>mjr</i>	3P	H.P. Gillis et al. "Low Energy Electron-Enhanced Etching of Si(100) in Hydrogen/Helium Direct-Current Plasma." Appl. Phys. Lett. 66 (19) May 8, 1995.					
<i>mjr</i>	3Q	H.P. Gillis et al. "The Dry Etching of Group III-Nitride Wide-Bandgap Semiconductors" Journal of Materials 48 50-55 (1996).					
<i>mjr</i>	3R	H.P. Gillis et al "Low Energy Electron-Enhanced Etching of GaAs(100) In a Chlorine/Hydrogen DC Plasma." Appl. Phys. Lett 68(16) Apr. 15, 1996.					
<i>mjr</i>	3S	H.P. Gillis et al "Low Energy Electron-Enhanced Etching of GaN/Si in Hydrogen Direct Current Plasma" J. Electrochem Soc. Vol 143. No. 11 Nov. 1996.					
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EXAMINER'S SIGNATURE: <i>Maurice P. Francis</i>				DATE CONSIDERED: <i>6/4/2005</i>			

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<i>msc</i>	4A	5,631,978	5/20/1997	Galand et al.	382	240	
<i>msc</i>	4B	5,660,744	8/26/1997	Sekine et al.	219	121.43	
<i>msc</i>	4C	5,882,538	3/16/1999	Martin et al.	216	71	
<i>msc</i>	4D	5,890,102	3/30/1999	Kossentini et al.	702	181	
<i>msc</i>	4E	5,906,684	05/19/99	Tamura et al.	118	728	
<i>msc</i>	4F	5,917,285	6/29/1999	Gillis et al.	313	632	
<i>msc</i>	4G	5,983,828	11/1999	Savas, Stephen E.	118	7231	
<i>msc</i>	4H	6,033,587	3/7/2000	Martin et al.	216	71	
<i>msc</i>	4I	6,231,777	05/2001	Kofuji et al.	216	71	
<i>msc</i>	4J	6,258,287	7/10/2001	Martin et al.	216	71	

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	4K						
	4L						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>msc</i>	4M	H.P. Gillis et al "Highly Anisotropic, Ultra-smooth Patterning of GaN/SiC by Low Energy Electron Enhanced Etching in DC Plasma" J. Electronic Mat 26, 301-305 (1997) pp 1-16.
	4N	
	4O	

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EXAMINER'S SIGNATURE: <i>Maureen J. O'Connell</i>	DATE CONSIDERED: <i>6/4/2005</i>
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